

**Erratum: Flatband Conditions Observed for Lanthanide-Silicide Monolayers
on *n*-Type Si(111)
[Phys. Rev. Lett. 82, 1927 (1999)]**

S. Vandré, T. Kalka, C. Preinesberger, and M. Dähne-Prietsch

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After the publication of our Letter, it was brought to our attention that Tuilier *et al.* [1] observed a Schottky-barrier height of 0.13 ± 0.05 eV for an ErSi₂ monolayer, which is comparable to our value of 0.08 ± 0.05 eV. Thus our statement that we observed such a low barrier height for the first time cannot be maintained, at least for the case of ErSi₂. We had not been aware of the work by Tuilier *et al.* and regret this oversight.

[1] M. H. Tuilier, G. Gewinner, C. Pirri, P. Wetzel, D. Bolmont, and O. Heckmann, J. Phys. IV (Paris), Colloq. **C9**, 187 (1994).